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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING

FILM FORMING METHOD,

SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE

SAME

Group Art Unit: 2814

Examiner: K. Eaton

AMENDMENT IN RESPONSE TO OFFICE ACTION OF FEBRUARY 3, 2000

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Responsive to the office action of February 3, 2000, please amend the captioned application as follows:

IN THE SPECIFICATION:

Page 7, line 7, change "dyne/cm" to read --dyne/cm²--.

Page 12, line 12, change "dyne/cm" to read --dyne/cm²--.

Page 13, line 12, change "dyne/cm" to read --dyne/cm²--.

Page 20, line 21, change "dyne/cm" to read --dyne/cm²--.

Page 21, line 19, change "dyne/cm" to read --dyne/cm²--; and line 21, change "dyne/cm" to read --dyne/cm²--.

Page 22, line 16, change "dyne/cm" to read --dyne/cm²--.

Page 23, line 1, change "dyne/cm" to read --dyne/cm²--; and line 3, change "dyne/cm" to read --dyne/cm²--; and